

PSMN8R7-80PS

N-channel 80 V 8.7 mΩ standard level MOSFET in TO-220

Rev. 02 — 1 November 2010

Product data sheet

1. Product profile

1.1 General description

Standard level N-channel MOSFET in TO-220 package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive

1.3 Applications

- DC-to-DC converters
- Motor control
- Load switching
- Server power supplies

1.4 Quick reference data

Table 1. Quick reference data

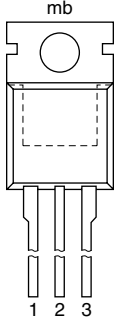
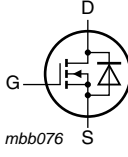
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25\text{ °C}; T_j \leq 175\text{ °C}$	-	-	80	V
I_D	drain current	$T_{mb} = 25\text{ °C}; V_{GS} = 10\text{ V};$ see Figure 1	-	-	90	A
P_{tot}	total power dissipation	$T_{mb} = 25\text{ °C};$ see Figure 2	-	-	170	W
T_j	junction temperature		-55	-	175	°C
Static characteristics						
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}; I_D = 10\text{ A};$ $T_j = 100\text{ °C};$ see Figure 12	-	-	14	mΩ
		$V_{GS} = 10\text{ V}; I_D = 10\text{ A};$ $T_j = 25\text{ °C};$ see Figure 13	[1]	-	7.5	8.7
Dynamic characteristics						
Q_{GD}	gate-drain charge	$V_{GS} = 10\text{ V}; I_D = 25\text{ A};$ $V_{DS} = 40\text{ V};$ see Figure 14 ;	-	11	-	nC
$Q_{G(tot)}$	total gate charge	see Figure 15	-	52	-	nC
Avalanche ruggedness						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$V_{GS} = 10\text{ V}; T_{j(init)} = 25\text{ °C};$ $I_D = 90\text{ A}; V_{sup} \leq 80\text{ V};$ $R_{GS} = 50\text{ Ω};$ unclamped	-	-	120	mJ

[1] Measured 3 mm from package.



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain		
3	S	source		
mb	D	mounting base; connected to drain		

SOT78 (TO-220AB)

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN8R7-80PS	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	80	V
V _{DGR}	drain-gate voltage	T _j ≥ 25 °C; T _j ≤ 175 °C; R _{GS} = 20 kΩ	-	80	V
V _{GS}	gate-source voltage		-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 100 °C; see Figure 1	-	64	A
		V _{GS} = 10 V; T _{mb} = 25 °C; see Figure 1	-	90	A
I _{DM}	peak drain current	pulsed; t _p ≤ 10 μs; T _{mb} = 25 °C; see Figure 3	-	361	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; see Figure 2	-	170	W
T _{stg}	storage temperature		-55	175	°C
T _j	junction temperature		-55	175	°C
T _{slid(M)}	peak soldering temperature		-	260	°C
Source-drain diode					
I _S	source current	T _{mb} = 25 °C	-	90	A
I _{SM}	peak source current	pulsed; t _p ≤ 10 μs; T _{mb} = 25 °C	-	361	A
Avalanche ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V _{GS} = 10 V; T _{j(init)} = 25 °C; I _D = 90 A; V _{sup} ≤ 80 V; R _{GS} = 50 Ω; unclamped	-	120	mJ

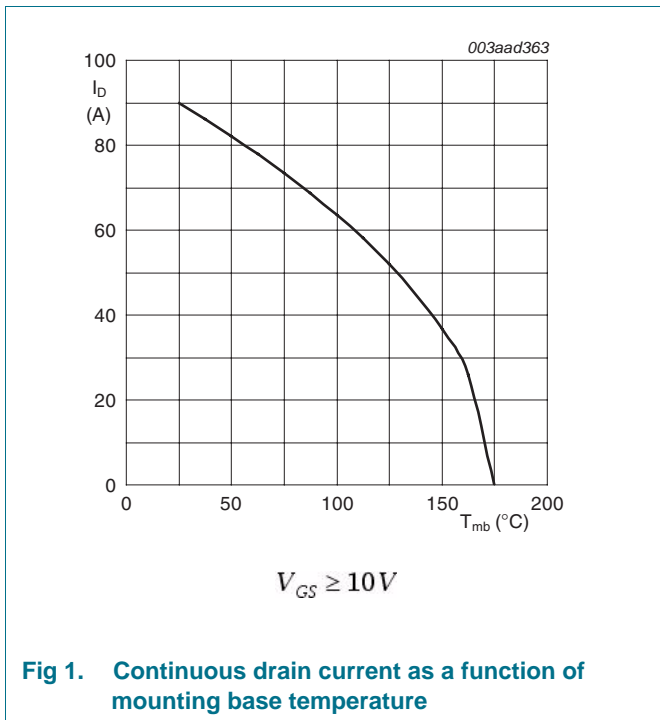


Fig 1. Continuous drain current as a function of mounting base temperature

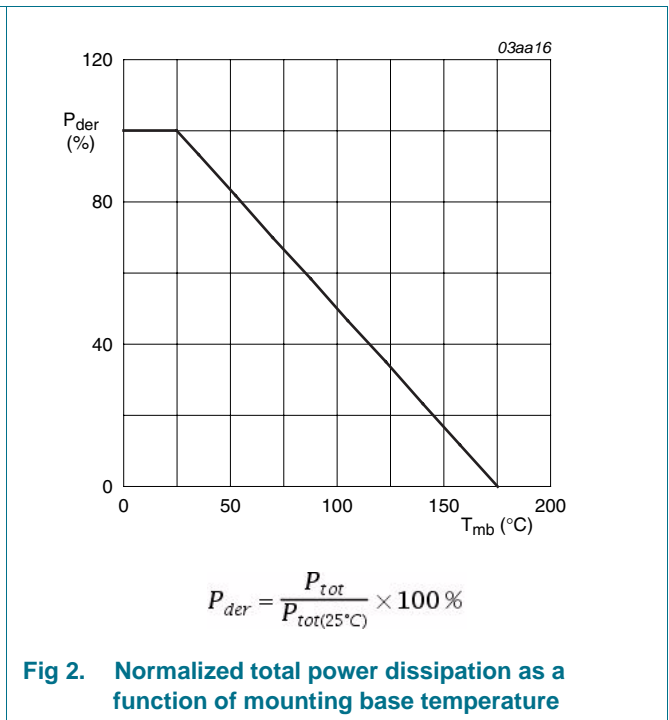


Fig 2. Normalized total power dissipation as a function of mounting base temperature

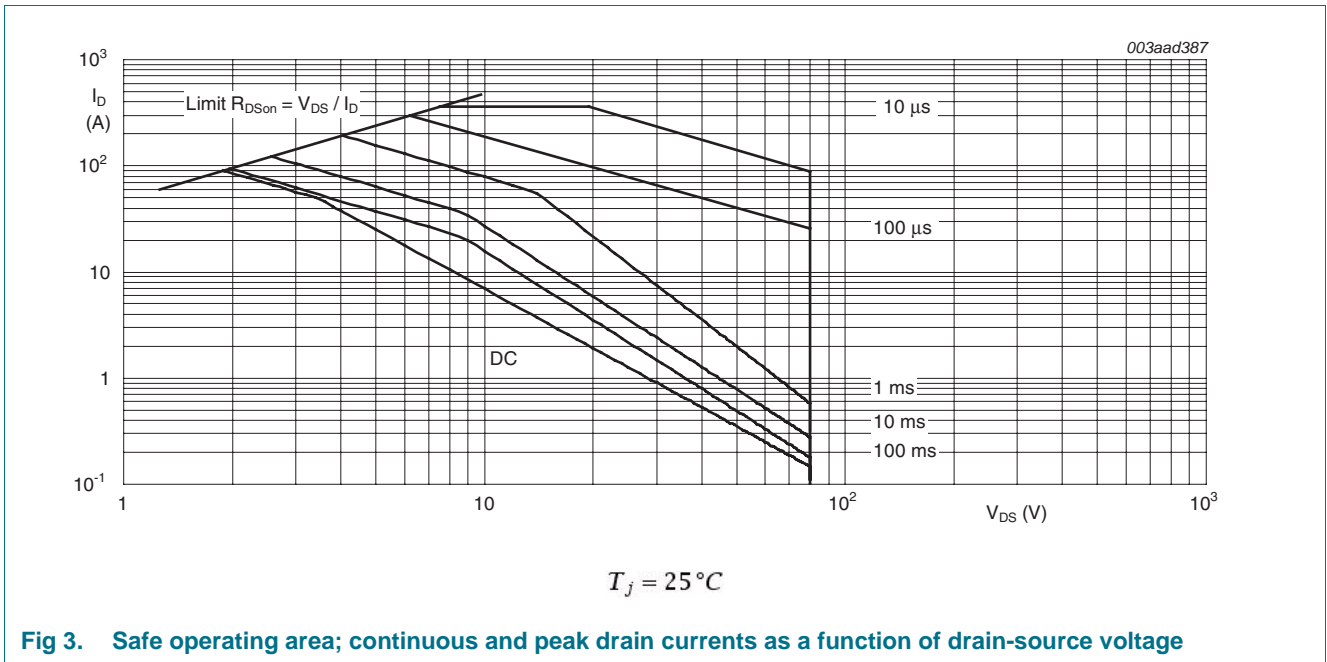
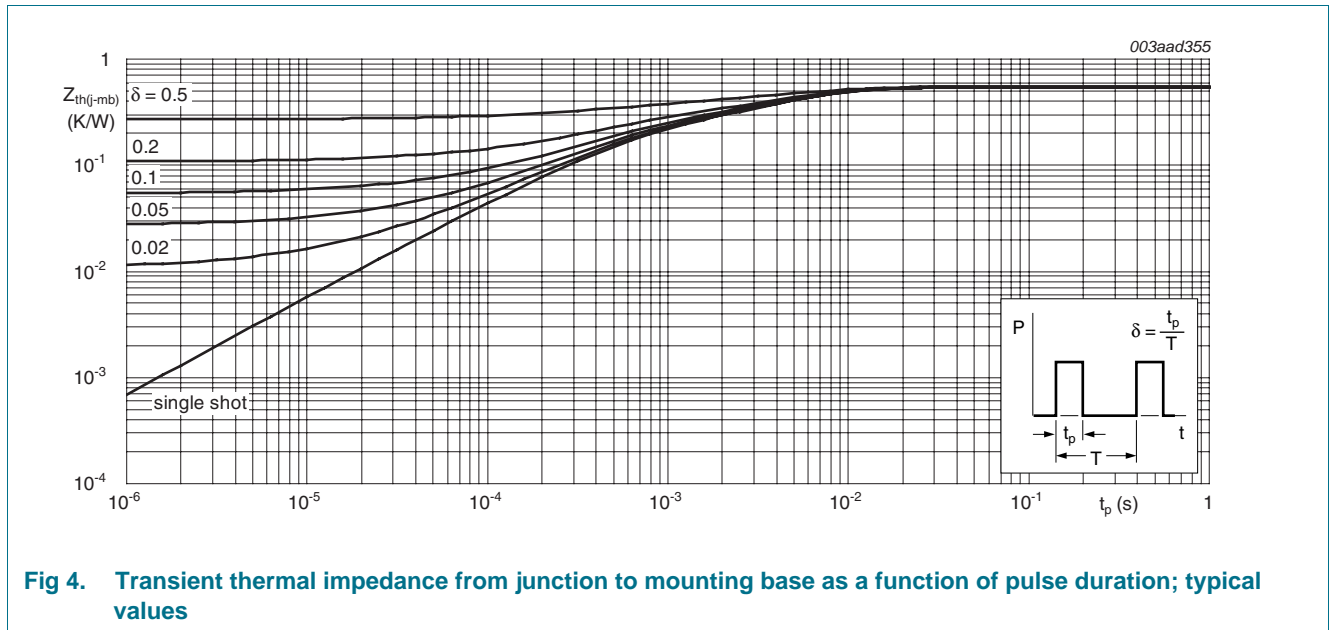


Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	0.54	0.88	K/W



6. Characteristics

Table 6. Characteristics

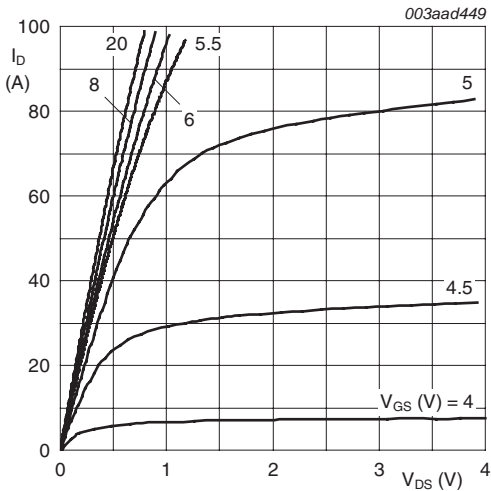
Tested to JEDEC standards where applicable.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
V _{(BR)DSS}	drain-source breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = -55 °C	73	-	-	V
		I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C	80	-	-	V
V _{GS(th)}	gate-source threshold voltage	I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 175 °C; see Figure 10	1	-	-	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = -55 °C; see Figure 10	-	-	4.6	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 25 °C; see Figure 11 ; see Figure 10	2.3	3	4	V
I _{DSS}	drain leakage current	V _{DS} = 80 V; V _{GS} = 0 V; T _j = 25 °C	-	0.3	5	μA
		V _{DS} = 80 V; V _{GS} = 0 V; T _j = 125 °C	-	-	100	μA
I _{GSS}	gate leakage current	V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	10	100	nA
		V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	10	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 10 A; T _j = 175 °C; see Figure 12	-	-	20.8 8	mΩ
		V _{GS} = 10 V; I _D = 10 A; T _j = 100 °C; see Figure 12	-	-	14	mΩ
		V _{GS} = 10 V; I _D = 10 A; T _j = 25 °C; see Figure 13	U	-	7.5	8.7
R _G	internal gate resistance (AC)	f = 1 MHz	-	1	-	Ω
Dynamic characteristics						
Q _{G(tot)}	total gate charge	I _D = 0 A; V _{DS} = 0 V; V _{GS} = 10 V	-	44	-	nC
		I _D = 25 A; V _{DS} = 40 V; V _{GS} = 10 V; see Figure 14 ; see Figure 15	-	52	-	nC
Q _{GS}	gate-source charge		-	15	-	nC
Q _{GS(th)}	pre-threshold gate-source charge	I _D = 25 A; V _{DS} = 40 V; V _{GS} = 10 V; see Figure 14	-	9.2	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge		-	5.8	-	nC
Q _{GD}	gate-drain charge	I _D = 25 A; V _{DS} = 40 V; V _{GS} = 10 V; see Figure 14 ; see Figure 15	-	11	-	nC
V _{GS(pl)}	gate-source plateau voltage	I _D = 25 A; V _{DS} = 40 V; see Figure 15	-	4.6	-	V
C _{iss}	input capacitance	V _{DS} = 40 V; V _{GS} = 0 V; f = 1 MHz; T _j = 25 °C; see Figure 16	-	3346	-	pF
C _{oss}	output capacitance		-	296	-	pF
C _{rss}	reverse transfer capacitance		-	158	-	pF
t _{d(on)}	turn-on delay time	V _{DS} = 40 V; R _L = 1.6 Ω; V _{GS} = 10 V; R _{G(ext)} = 4.7 Ω	-	21	-	ns
t _r	rise time		-	26	-	ns
t _{d(off)}	turn-off delay time		-	46	-	ns
t _f	fall time		-	20	-	ns
Source-drain diode						
V _{SD}	source-drain voltage	I _S = 10 A; V _{GS} = 0 V; T _j = 25 °C; see Figure 17	-	0.79	1.2	V

Table 6. Characteristics ...continued
Tested to JEDEC standards where applicable.

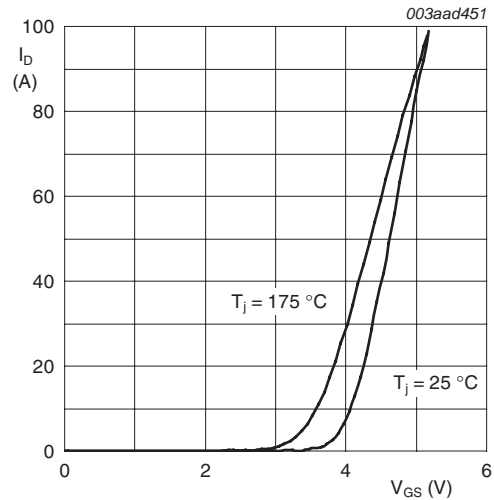
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
t_{rr}	reverse recovery time	$I_S = 25 \text{ A}$; $di_S/dt = 100 \text{ A}/\mu\text{s}$; $V_{GS} = 0 \text{ V}$; $V_{DS} = 40 \text{ V}$	-	42	-	ns
Q_r	recovered charge		-	66	-	nC

[1] Measured 3 mm from package.



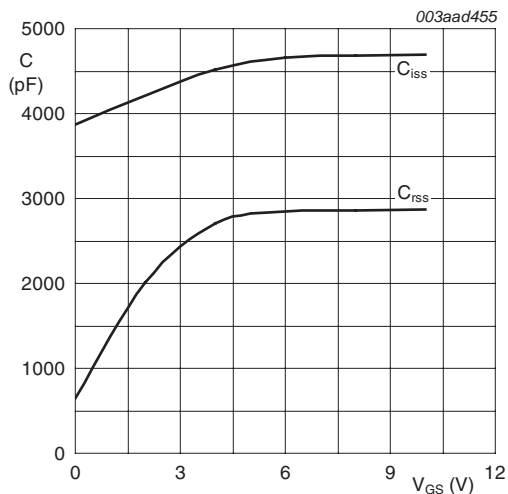
$T_j = 25^\circ\text{C}$

Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values



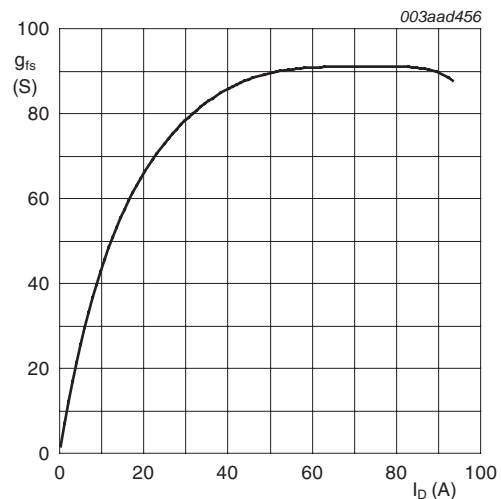
$V_{DS} > I_D \times R_{DS(on)}$

Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values



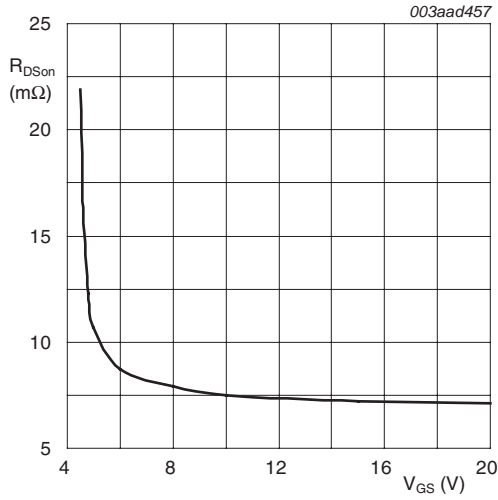
$V_{DS} = 0 \text{ V}; f = 1 \text{ MHz}$

Fig 7. Input and reverse transfer capacitances as a function of gate-source voltage; typical values



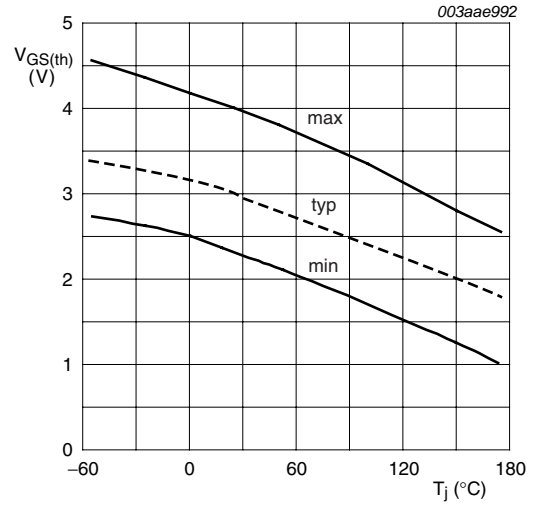
$T_j = 25^\circ\text{C}; V_{DS} = 15 \text{ V}$

Fig 8. Forward transconductance as a function of drain current; typical values



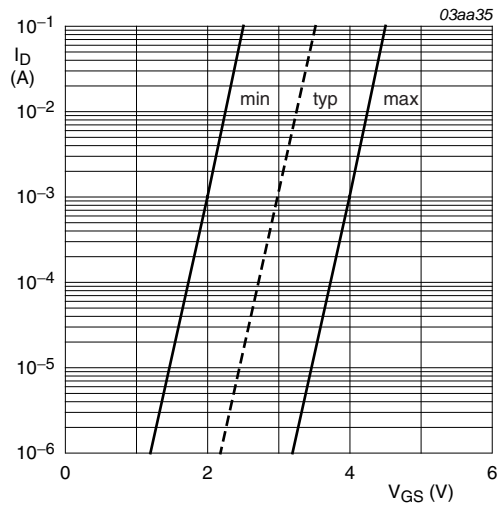
$$T_j = 25\text{ }^\circ\text{C}; I_D = 25\text{ A}$$

Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values



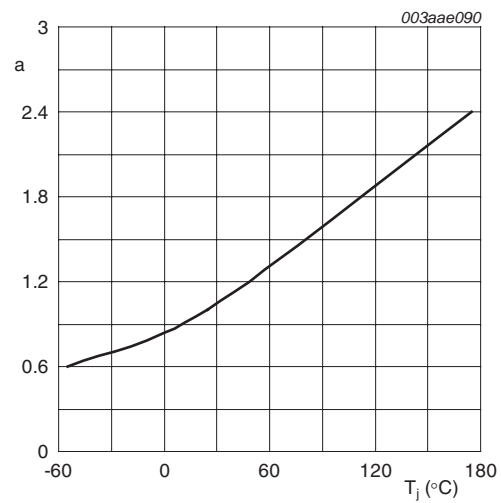
$$I_D = 1\text{ mA}; V_{DS} = V_{GS}$$

Fig 10. Gate-source threshold voltage as a function of junction temperature



$$T_j = 25\text{ }^\circ\text{C}; V_{DS} = 5\text{ V}$$

Fig 11. Sub-threshold drain current as a function of gate-source voltage



$$a = \frac{R_{DS(on)}}{R_{DS(on)@25^\circ\text{C}}}$$

Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature

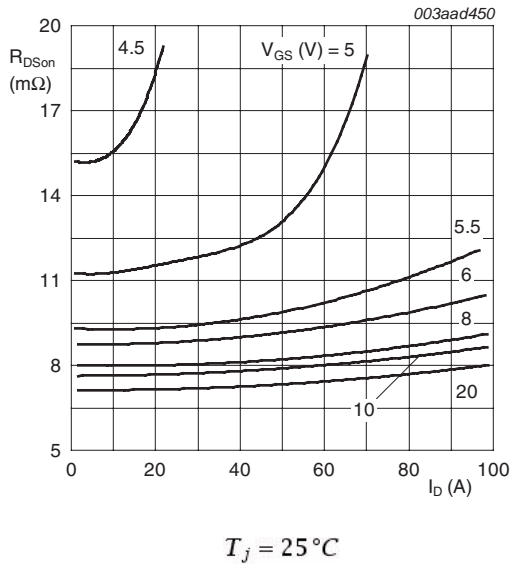


Fig 13. Drain-source on-state resistance as a function of drain current; typical values

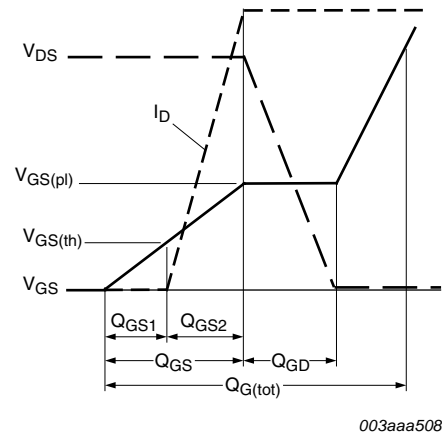


Fig 14. Gate charge waveform definitions

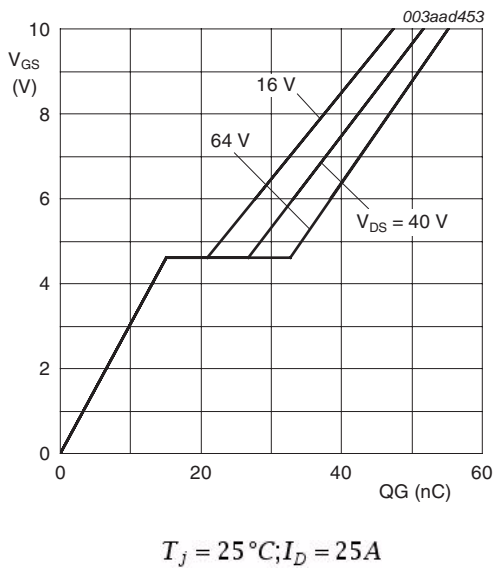


Fig 15. Gate-source voltage as a function of gate charge; typical values

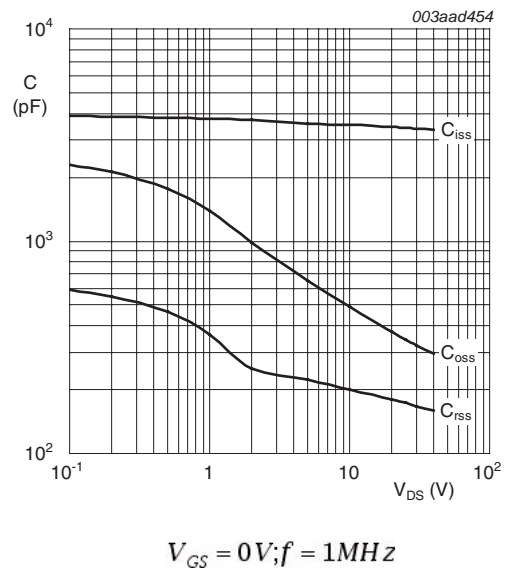


Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

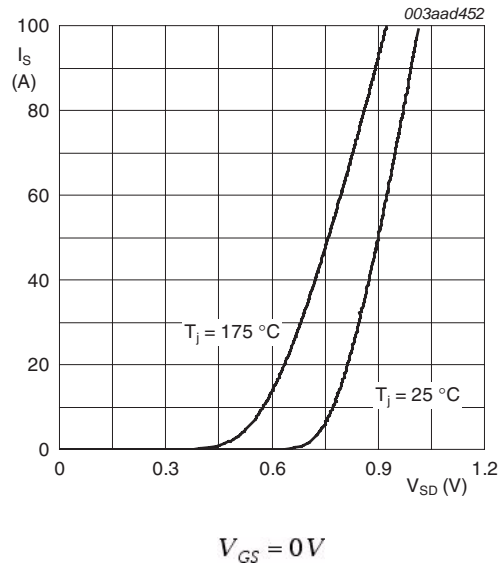


Fig 17. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

7. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB

SOT78

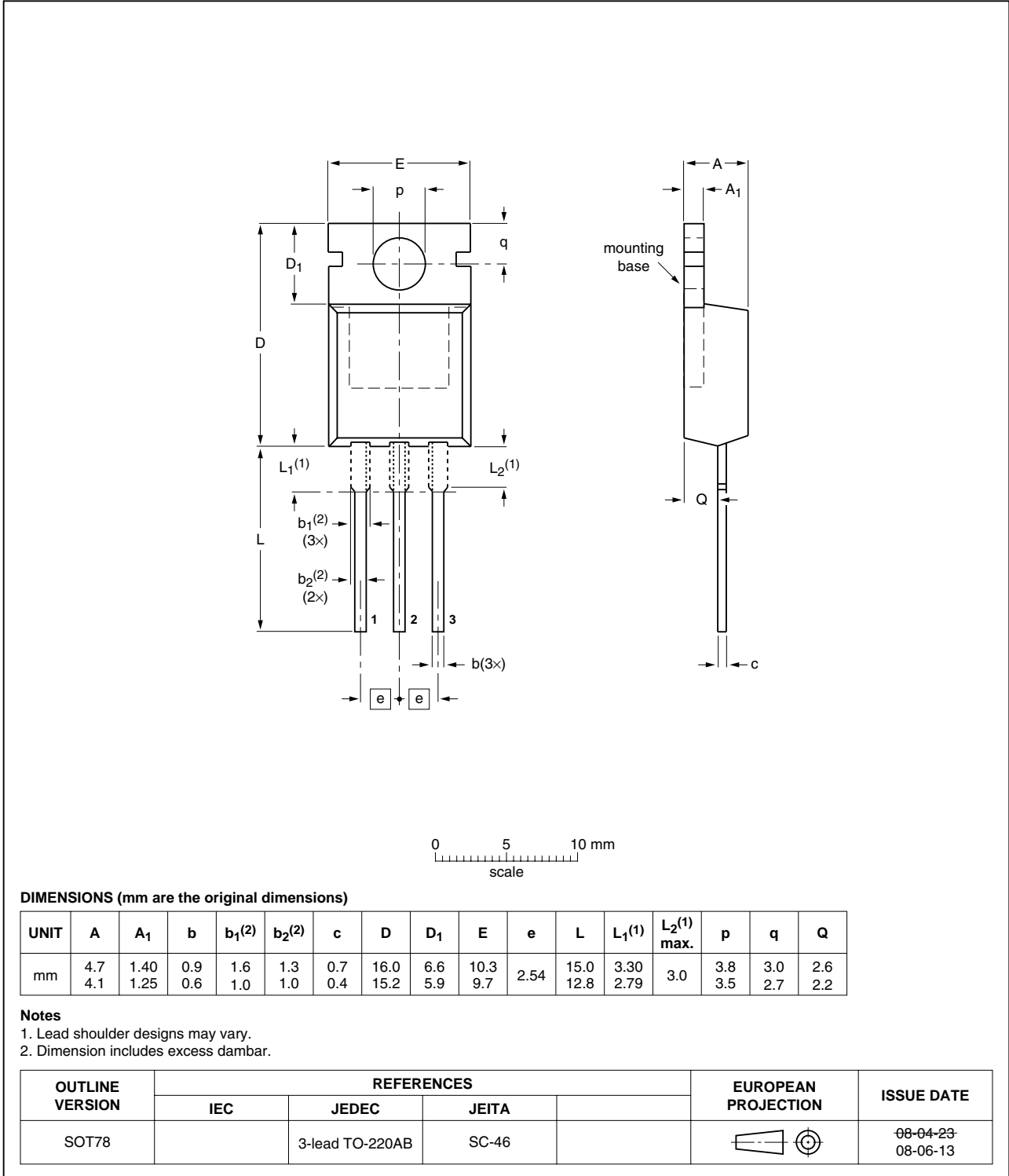


Fig 18. Package outline SOT78 (TO-220AB)

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN8R7-80PS v.2	20101101	Product data sheet	-	PSMN8R7-80PS v.1
Modifications:	<ul style="list-style-type: none">• Status changed from objective to product.• Various changes to content.			
PSMN8R7-80PS v.1	20100129	Objective data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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